

## **IN THE CLAIMS:**

Please amend the claims as shown below.

1-43 Cancelled

44. (new) A method of manufacturing an epitaxial silicon wafer, comprising: controlling an oxygen concentration in accordance with a change in a nitrogen concentration based on a characteristic that the nitrogen concentration increases from a shoulder portion to a tail portion of a silicon ingot, so that the oxygen concentration and the nitrogen concentration fall within a concentration range where an upper limit is defined by a line connecting a point at which the nitrogen concentration is  $3 \times 10^{15}$  atoms/cm<sup>3</sup> when the oxygen concentration is  $7 \times 10^{17}$  atoms/cm<sup>3</sup> and a point at which the nitrogen concentration is  $3 \times 10^{14}$  atoms/cm<sup>3</sup> when the oxygen concentration is  $1.6 \times 10^{18}$  atoms/cm<sup>3</sup>, within the concentration range where the oxygen concentration and the nitrogen concentration are plotted along the horizontal axis and the vertical axis, at the same time when the silicon ingot is pulled up from a silicon raw material melt doped with nitrogen so that the nitrogen concentration at the tail portion of the silicon ingot is less than  $3 \times 10^{15}$  atoms/cm<sup>3</sup>;

obtaining the silicon wafer by slicing the pulled-up silicon ingot; and

subjecting the obtained silicon wafer to epitaxial growth processing.